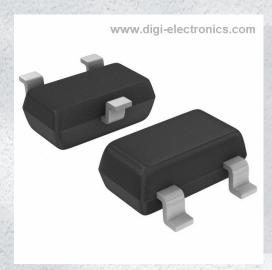


MUN2112T1G Datasheet



https://www.DiGi-Electronics.com

DiGi Electronics Part Number

MUN2112T1G-DG

Manufacturer

onsemi

Manufacturer Product Number

MUN2112T1G

Description

TRANS PREBIAS PNP 50V 0.1A SC59

Detailed Description

Pre-Biased Bipolar Transistor (BJT) PNP - Pre-Biase d 50 V 100 mA 230 mW Surface Mount SC-59



Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

DiGi is a global authorized distributor of electronic components.



Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
MUN2112T1G	onsemi
Series:	Product Status:
	Active
Transistor Type:	Current - Collector (Ic) (Max):
PNP - Pre-Biased	100 mA
Voltage - Collector Emitter Breakdown (Max):	Resistor - Base (R1):
50 V	22 kOhms
Resistor - Emitter Base (R2):	DC Current Gain (hFE) (Min) @ Ic, Vce:
22 kOhms	60 @ 5mA, 10V
Vce Saturation (Max) @ lb, lc:	Current - Collector Cutoff (Max):
250mV @ 300μA, 10mA	500nA
Power - Max:	Mounting Type:
230 mW	Surface Mount
Package / Case:	Supplier Device Package:
TO-236-3, SC-59, SOT-23-3	SC-59
Base Product Number:	
MUN2112	

Environmental & Export classification

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	
8541.21.0095	



Digital Transistors (BRT) $R1 = 22 k\Omega, R2 = 22 k\Omega$

MUN2112, MMUN2112L, **MUN5112, DTA124EE,** DTA124EM3, NSBA124EF3

PNP Transistors with Monolithic Bias Resistor Network

This series of digital transistors is designed to replace a single device and its external resistor bias network. The Bias Resistor Transistor (BRT) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a baseemitter resistor. The BRT eliminates these individual components by integrating them into a single device. The use of a BRT can reduce both system cost and board space.

Features

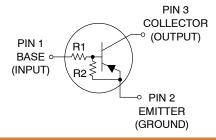
- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS $(T_A = 25^{\circ}C)$

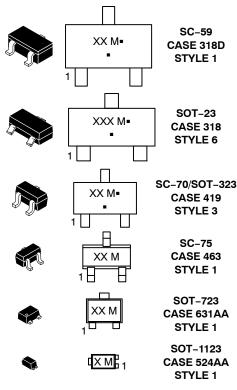
Rating	Symbol	Max	Unit
Collector-Base Voltage	V_{CBO}	50	Vdc
Collector-Emitter Voltage	V_{CEO}	50	Vdc
Collector Current – Continuous	Ic	100	mAdc
Input Forward Voltage	V _{IN(fwd)}	40	Vdc
Input Reverse Voltage	V _{IN(rev)}	10	Vdc

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

PIN CONNECTIONS



MARKING DIAGRAMS



XXX = Specific Device Code = Date Code* M

= Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering, marking, and shipping information in the package dimensions section on page 2 of this data sheet.

1

^{*}Date Code orientation may vary depending upon manufacturing location.

Table 1. ORDERING INFORMATION

Device	Part Marking	Package	Shipping [†]
MUN2112T1G, NSVMUN2112T1G	6B	SC-59 (Pb-Free)	3000 / Tape & Reel
MMUN2112LT1G, NSVMMUN2112LT1G	A6B	SOT-23 (Pb-Free)	3000 / Tape & Reel
MUN5112T1G, SMUN5112T1G	6B	SC-70/SOT-323 (Pb-Free)	3000 / Tape & Reel
DTA124EET1G	6B	SC-75 (Pb-Free)	3000 / Tape & Reel
DTA124EM3T5G	6B	SOT-723 (Pb-Free)	8000 / Tape & Reel
NSBA124EF3T5G	Y	SOT-1123 (Pb-Free)	8000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

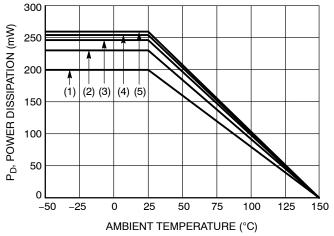


Figure 1. Derating Curve

- (1) SC-75 and SC-70/SOT-323; Minimum Pad
- (2) SC-59; Minimum Pad
- (3) SOT-23; Minimum Pad
- (4) SOT-1123; 100 mm², 1 oz. copper trace
- (5) SOT-723; Minimum Pad

Table 2. THERMAL CHARACTERISTICS

	Characteristic	Symbol	Max	Unit
THERMAL CHARACTERISTI	CS (SC-59) (MUN2112)	•		
Total Device Dissipation $T_A = 25^{\circ}C \qquad \text{(Note 1)}$ (Note 2) Derate above 25°C	(Note 1)	P _D	230 338 1.8	mW mW/°C
(Note 2) Thermal Resistance,	(Note 1)	R _{0JA}	2.7 540	°C/W
Junction to Ambient	(Note 2)		370	
Thermal Resistance, Junction to Lead (Note 2)	(Note 1)	$R_{ hetaJL}$	264 287	°C/W
Junction and Storage Temper	ature Range	T_J , T_{stg}	-55 to +150	°C
THERMAL CHARACTERISTIC	CS (SOT-23) (MMUN2112L)			
Total Device Dissipation $T_A = 25^{\circ}C \qquad \text{(Note 1)}$ (Note 2)		P _D	246 400	mW
Derate above 25°C (Note 2)	(Note 1)		2.0 3.2	mW/°C
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	$R_{ hetaJA}$	508 311	°C/W
Thermal Resistance, Junction to Lead (Note 2)	(Note 1)	$R_{ hetaJL}$	174 208	°C/W
Junction and Storage Temper	ature Range	T _J , T _{stg}	-55 to +150	°C
THERMAL CHARACTERISTIC	CS (SC-70/SOT-323) (MUN5112)			
Total Device Dissipation T _A = 25°C (Note 1) (Note 2)		P _D	202 310	mW
Derate above 25°C (Note 2)	(Note 1)		1.6 2.5	mW/°C
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	$R_{ hetaJA}$	618 403	°C/W
Thermal Resistance, Junction to Lead (Note 2)	(Note 1)	$R_{ hetaJL}$	280 332	°C/W
Junction and Storage Temper	ature Range	T _J , T _{stg}	-55 to +150	°C
THERMAL CHARACTERISTIC	CS (SC-75) (DTA124EE)			
Total Device Dissipation T _A = 25°C (Note 1)		P _D	200	mW
(Note 2) Derate above 25°C (Note 2)	(Note 1)		300 1.6 2.4	mW/°C
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	$R_{ hetaJA}$	600 400	°C/W
Junction and Storage Temper	ature Range	T _J , T _{stg}	-55 to +150	°C
THERMAL CHARACTERISTIC	CS (SOT-723) (DTA124EM3)	·		
Total Device Dissipation $T_A = 25^{\circ}C$ (Note 1)		P _D	260	mW
(Note 2) Derate above 25°C (Note 2)	(Note 1)		600 2.0 4.8	mW/°C
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	$R_{ heta JA}$	480 205	°C/W
Junction and Storage Temper	ature Range	T _J , T _{stg}	-55 to +150	°C

- 1. FR-4 @ Minimum Pad.
- 2. FR-4 @ 1.0 x 1.0 Inch Pad.
- FR-4 @ 100 mm², 1 oz. copper traces, still air.
 FR-4 @ 500 mm², 1 oz. copper traces, still air.

Table 2. THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
THERMAL CHARACTERISTICS (SOT-1123) (NSBA124EF3)			•
Total Device Dissipation T _A = 25°C (Note 3) (Note 4) Derate above 25°C (Note 3) (Note 4)	P _D	254 297 2.0 2.4	mW mW/°C
Thermal Resistance, (Note 3) Junction to Ambient (Note 4)	$R_{ hetaJA}$	493 421	°C/W
Thermal Resistance, Junction to Lead (Note 3)	$R_{ heta JL}$	193	°C/W
Junction and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C

- 1. FR-4 @ Minimum Pad.
- 2. FR-4 @ 1.0 x 1.0 Inch Pad.
- FR-4 @ 100 mm², 1 oz. copper traces, still air.
 FR-4 @ 500 mm², 1 oz. copper traces, still air.

Table 3. FLECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS		•			
Collector–Base Cutoff Current $(V_{CB} = 50 \text{ V}, I_E = 0)$	I _{CBO}	_	_	100	nAdc
Collector–Emitter Cutoff Current (V _{CE} = 50 V, I _B = 0)	I _{CEO}	_	_	500	nAdc
Emitter-Base Cutoff Current (V _{EB} = 6.0 V, I _C = 0)	I _{EBO}	_	-	0.2	mAdc
Collector–Base Breakdown Voltage $(I_C = 10 \mu A, I_E = 0)$	V _(BR) CBO	50	_	-	Vdc
Collector–Emitter Breakdown Voltage (Note 5) (I _C = 2.0 mA, I _B = 0)	V _(BR) CEO	50	-	-	Vdc
ON CHARACTERISTICS	·				
DC Current Gain (Note 5) (I _C = 5.0 mA, V _{CE} = 10 V)	h _{FE}	60	100	-	
Collector–Emitter Saturation Voltage (Note 5) (I _C = 10 mA, I _B = 0.3 mA)	V _{CE(sat)}	_	-	0.25	Vdc
Input Voltage (off) ($V_{CE} = 5.0 \text{ V}, I_{C} = 100 \mu\text{A}$)	V _{i(off)}	_	1.2	0.8	Vdc
Input Voltage (on) ($V_{CE} = 0.3 \text{ V}, I_{C} = 5.0 \text{ mA}$)	V _{i(on)}	2.5	1.7	-	Vdc
Output Voltage (on) (V _{CC} = 5.0 V, V _B = 2.5 V, R _L = 1.0 k Ω)	V _{OL}	_	-	0.2	Vdc
Output Voltage (off) (V _{CC} = 5.0 V, V _B = 0.5 V, R _L = 1.0 k Ω)	V _{OH}	4.9	_	-	Vdc
Input Resistor	R1	15.4	22	28.6	kΩ
Resistor Ratio	R ₁ /R ₂	0.8	1.0	1.2	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

5. Pulsed Condition: Pulse Width = 300 msec, Duty Cycle ≤ 2%.

TYPICAL CHARACTERISTICS MUN2112, MMUN2112L, MUN5112, DTA124EE, DTA124EM3

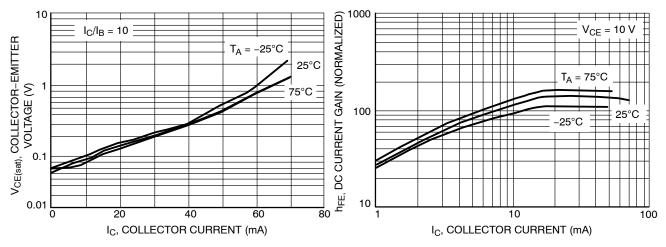
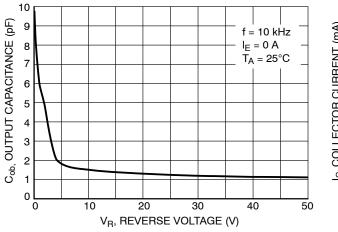
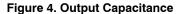


Figure 2. V_{CE(sat)} vs. I_C

Figure 3. DC Current Gain





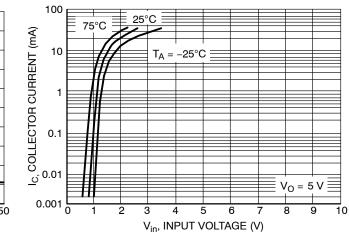


Figure 5. Output Current vs. Input Voltage

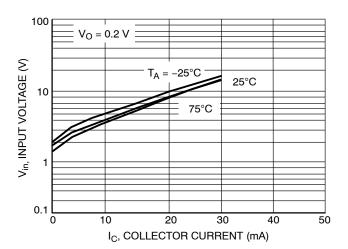


Figure 6. Input Voltage vs. Output Current

TYPICAL CHARACTERISTICS - NSBA124EF3

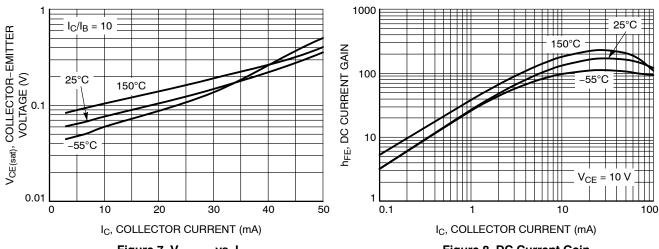


Figure 7. V_{CE(sat)} vs. I_C

Figure 8. DC Current Gain

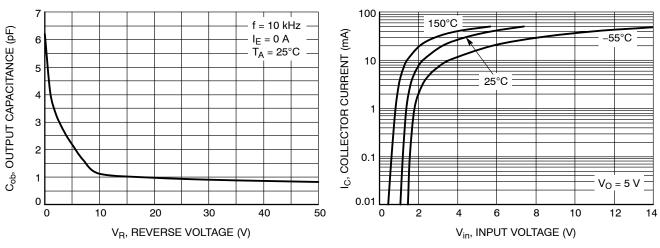


Figure 9. Output Capacitance

Figure 10. Output Current vs. Input Voltage

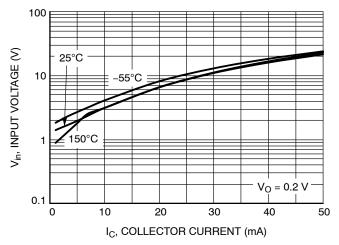


Figure 11. Input Voltage vs. Output Current



MILLIMETERS

MIN

0.89

0.01

0.37

0.08

2.80

1.20

1.78

0.30

0.35

2.10

O°

NOM

1.00

0.06

0.44

0.14

2.90

1.30

1.90

0.43

0.54

2.40

PACKAGE DIMENSIONS



SOT-23 (TO-236) 2.90x1.30x1.00 1.90P **CASE 318 ISSUE AU**

DATE 14 AUG 2024

MAX

1.11

0.10

0.50

0.20

3.04

1.40

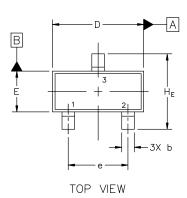
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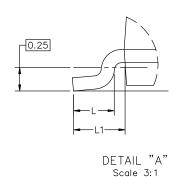
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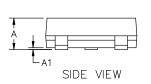
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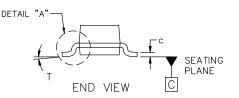
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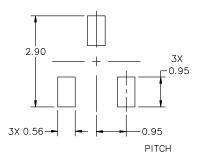
10°













DIM

Α

Α1

b

С

D

Ε

е L

L1

HE

Τ

- DIMENSIONING AND TOLERANCING 1.
- PER ASME Y14.5M, 2018. CONTROLLING DIMENSIONS: MILLIMETERS.
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE
- BASE MATERIAL.
 DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code

= Date Code

= Pb-Free Package

RECOMMENDED MOUNTING FOOTPRINT

* For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

DOCUMENT NUMBER:	98ASB42226B	Electronic versions are uncontrolled except when accessed directly from the Document R Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.			
DESCRIPTION:	SOT-23 (TO-236) 2.90x1.30x1.00 1.90P		PAGE 1 OF 2		

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^{*}This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "=", may or may not be present. Some products may not follow the Generic Marking.

SOT-23 (TO-236) 2.90x1.30x1.00 1.90P CASE 318 ISSUE AU

DATE 14 AUG 2024

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: STYLE 8: PIN 1. EMITTER PIN 1. ANOD 2. BASE 2. NO CC 3. COLLECTOR 3. CATHO	ONNECTION	
STYLE 9: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 10: PIN 1. DRAIN 2. SOURCE 3. GATE	STYLE 11: STYLE 12: PIN 1. ANODE PIN 1. CATHO 2. CATHODE 2. CATHO 3. CATHODE-ANODE 3. ANODO	ODE 2. DRAIN 2. GATE	
STYLE 15: PIN 1. GATE 2. CATHODE 3. ANODE	STYLE 16: PIN 1. ANODE 2. CATHODE 3. CATHODE	STYLE 17: STYLE 18: PIN 1. NO CONNECTION PIN 1. NO CO 2. ANODE 2. CATHO 3. CATHODE 3. ANODO	ODE 2. ANODE 2. ANODE	
STYLE 21: PIN 1. GATE 2. SOURCE 3. DRAIN	STYLE 22: PIN 1. RETURN 2. OUTPUT 3. INPUT	STYLE 23: STYLE 24: PIN 1. ANODE PIN 1. GATE 2. ANODE 2. DRAIN 3. CATHODE 3. SOURCE		CTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE			

DOCUMENT NUMBER:	98ASB42226B	Electronic versions are uncontrolled except when accessed directly from the Document Rep Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.			
DESCRIPTION:	SOT-23 (TO-236) 2.90x1.30x1.00 1.90P		PAGE 2 OF 2		

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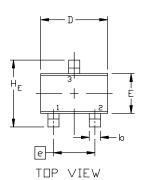
PACKAGE DIMENSIONS

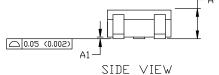


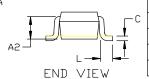
DATE 11 OCT 2022



SCALE 4:1







NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH

	MILLIMETERS				INCHES	
DIM	MIN.	N□M.	MAX.	MIN.	N□M.	MAX.
Α	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2		0.70 REF			0.028 BS	C
b	0.30	0.35	0.40	0.012	0.014	0.016
С	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.00	2.20	0.071	0.080	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
е	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65 BSC				0.026 BS	C
L	0.20	0.38	0.56	0.008	0.015	0.022
HE	2.00	2.10	2.40	0.079	0.083	0.095



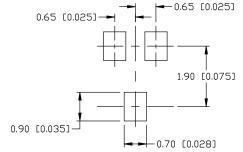


XX = Specific Device Code

Μ = Date Code

= Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.



For additional information on our Pb-Free strategy and soldering details, please download the IIN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

SOLDERING FOOTPRINT

STYLE 1: CANCELLED	STYLE 2: PIN 1. ANODE 2. N.C. 3. CATHODE	STYLE 3: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 5: PIN 1. ANODE 2. ANODE 3. CATHODE	
STYLE 6:	STYLE 7:	STYLE 8:	STYLE 9:	STYLE 10:	STYLE 11:
PIN 1. EMITTER	PIN 1. BASE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. CATHODE
2. BASE	2. EMITTER	2. SOURCE	2. CATHODE	2. ANODE	CATHODE
COLLECTOR	COLLECTOR	3. DRAIN	CATHODE-ANODE	3. ANODE-CATHODE	CATHODE

DOCUMENT NUMBER:	98ASB42819B	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	SC-70 (SOT-323)		PAGE 1 OF 1

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PACKAGE DIMENSIONS

SC75-3 1.60x0.80x0.80, 1.00P

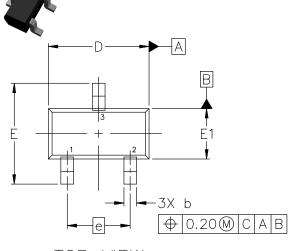
CASE 463 ISSUE H

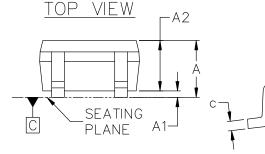
DATE 01 FEB 2024

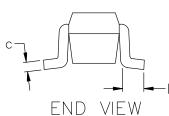
NOTES:

- DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5-2018.
- ALL DIMENSION ARE IN MILLIMETERS.

DIM	М	ILLIMETER	RS
	MIN.	NOM.	MAX.
А	0.70	0.80	0.90
A1	0.00	0.05	0.10
A2	(0.80 REF	
Ь	0.15	0.20	0.30
С	0.10	0.15	0.25
D	1.55	1.60	1.65
E	1.50	1.60	1.70
E1	0.70	0.80	0.90
е		1.00 BSC	,
L	0.10	0.15	0.20







SIDE VIEW

GENERIC MARKING DIAGRAM*



XX = Specific Device Code

Μ = Date Code

= Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:	
PIN 1. BASE	
O ENTITED	

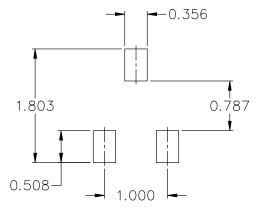
3 COLLECTOR

STYLE 2: PIN 1. ANODE 2. N/C 3. CATHODE

> GATE SOURCE DRAIN

STYLE 3: PIN 1. ANODE 2. ANODE

3 CATHODE



RECOMMENDED MOUNTING FOOTPRINT*

FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

STYLE 4:	STYLE 5:
PIN 1. CATHODE	PIN 1. 0
2. CATHODE	2. 8
3. ANODE	3. E

DOCUMENT NUMBER: 98ASB15184C

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DESCRIPTION:

SC75-3 1.60x0.80x0.80, 1.00P

PAGE 1 OF 1

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PACKAGE DIMENSIONS

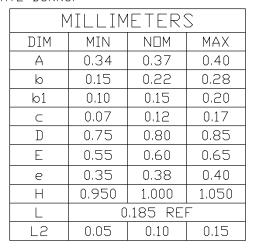


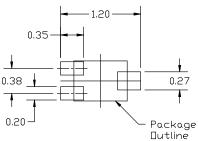
SOT-1123 0.80x0.60x0.37, 0.35P CASE 524AA ISSUE D

DATE 18 JAN 2024

NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
- CONTROLLING DIMENSION: MILLIMETERS. 2.
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

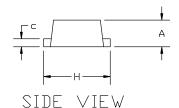


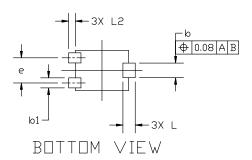


RECOMMENDED MOUNTING FOOTPRINT

*For additional information on our Pb-Free strategy and soldering details, please download the IN Semiconductor Soldering and Mounting Techniques Reference manual, SOLDERRM/D.

В ТПР VIEW





GENERIC MARKING DIAGRAM*



= Specific Device Code = Date Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:
PIN 1. BASE
EMITTER
3 COLLECTOR

STYLE 2: PIN 1. ANODE 2. N/C 3. CATHODE

STYLE 3: PIN 1. ANODE 2. ANODE 3. CATHODE

STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE

STYLE 5: PIN 1. GATE 2. SOURCE

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DESCRIPTION:	SOT-1123 0.80x0.60x0.37, 0.35P		PAGE 1 OF 1

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PACKAGE DIMENSIONS



SOT-723 1.20x0.80x0.50, 0.40P CASE 631AA ISSUE E

DATE 24 JAN 2024

MAX.

0.55

0.27

0.37

0.17

1.25

0.85

1.25

0.25

MILLIMETERS

 $N\square M$.

0.50

0.21

0.31

0.12

1.20

0.80

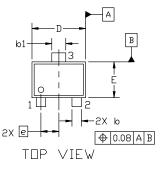
0.40 BSC

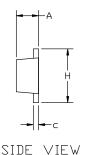
1.20

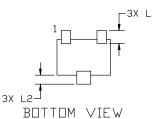
0.29 REF

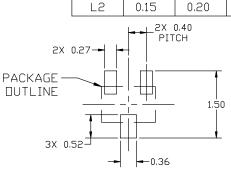
NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
- 2. CONTROLLING DIMENSION: MILLIMETERS.
- 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.









DIM

Α

b

b1

c D

Ε

e H

L

MIN.

0.45

0.15

0.25

0.07

1.15

0.75

1.15

RECOMMENDED MOUNTING FOOTPRINT

*For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

GENERIC MARKING DIAGRAM*



XX = Specific Device Code M = Date Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1: STYLE 2: STYLE 3: STYLE 4: STYLE 5: PIN 1. GATE 2. SOURCE PIN 1. BASE PIN 1. ANODE PIN 1. ANODE PIN 1. CATHODE 2 FMITTER 2 CATHODE 2 N/C 2. ANODE 3. COLLECTOR 3. CATHODE 3. CATHODE 3. DRAIN

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